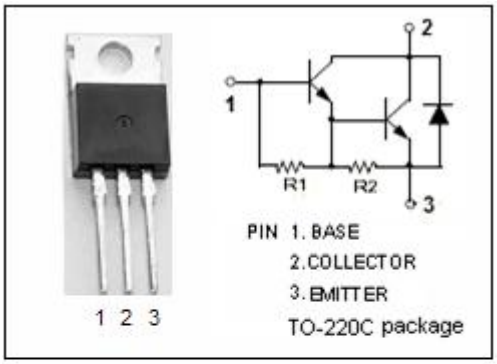
isc Silicon NPN Darlington Power Transistor BU920T

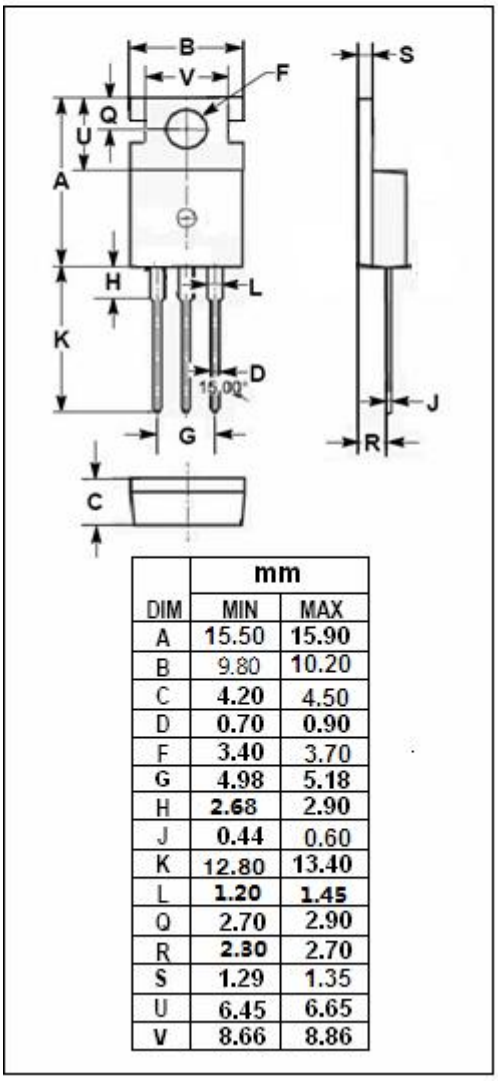
DESCRIPTION

- High Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for automotive ignition applications and inverter circuits for motor control.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage V_{BE}= 0	400	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	10	A
I_{CM}	Collector Current-peak	15	A
I_B	Base Current	5	A
P_C	Collector Power Dissipation @T_C=25℃	105	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.2	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	350			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 50mA			1.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 7A; I_B= 140mA			1.8	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 50mA			2.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 7A; I_B= 140mA			2.5	V
I_{CES}	Collector Cutoff Current	V_{CE}= 400V;V_{BE}= 0 V_{CE}= 400V;V_{BE}= 0;T_j= 125℃			0.25 0.5	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 350V; I_B= 0			0.25	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			50	mA
V_{ECF}	C-E Diode Forward Voltage	I_F= 7A			2.5	V